ISL73847SEH

Single Event Effects (SEE) Testing of the ISL73847SEH Synchronous Buck Controller

Introduction

The intense proton and heavy ion environment encountered in space applications can cause a variety of Destructive Single Event Effects (DSEE) in electronic circuitry, including Single Event Upset (SEU), Single Event Transient (SET), Single Event Functional Interrupt (SEFI), Single Event Latch-Up (SEL), Single Event Gate Rupture (SEGR), and Single Event Burnout (SEB). SEE can lead to system-level performance issues including disruption, degradation, and destruction. For predictable and reliable space system operation, individual electronic components should be characterized to determine their SEE response. This report discusses the results of SEE testing performed on the ISL73847SEH product. The ISL73847SEH is offered with radiation assurance screening to 75krad(Si) at 10mrad(Si)/s.

SEE Test Result Overview

The ISL73847SEH proved to be free of DSEE including SEL at a VDD voltage of 25.0V and a case temperature of 125°C when irradiated with normal incidence Gold (^{197}Au) at a Linear Energy Transfer (LET) of 86MeV·cm^2/mg. The device was also free of DSEE including SEL at a VCC voltage of 6.7V. Additionally, the ISL73847SEH proved to be free of SEFIs at a ISENSE voltage of 10V. The 2-phase buck output of 1.0V was loaded to a total of 5A.

The buck regulator was tested for SEE at switching frequencies (f_{SW}) of 500kHz and 1000kHz, each requiring separate board assemblies. The 500kHz configuration used an output inductor (L_{OUTx}) of 1µH an output capacitor (C_{OUT}) of 880µF. No SET deviations exceeding ±20mV (±2% on the 1.0V output with 5.0A load) were captured. The1000kHz configuration used an output inductor (L_{OUTx}) of 0.56µH an output capacitor (C_{OUT}) of 880µF.

One SET event with a deviation greater than ±20mV was observed, which showed as a missing pulse on PWM output. The DSEE testing were performed on twelve devices, four each for VDD, VCC, and ISENSE testing. The SET testing was performed on two devices at a f_{SW} of 500kHz and another two at an f_{SW} of 1000kHz. Each of the device runs were irradiated with normal incidence gold for a LET of 86MeV•cm^2/mg to a fluence of 1E7particle/cm^2. See Table 2, Table 3, Table 4, and Table 5 for more details.

Product Description

The ISL73847SEH is a synchronous buck controller that can operate as a single or dual-phase controller. It is intended to work with the ISL73041SEH (half-bridge GaN FET driver) to generate point-of-load voltage rails for radiation-hardened space applications.

It accepts an input voltage range of 4.5V to 19V with a programmable output switching frequency between 250kHz and 1.5MHz set with a single resistor. The output can regulate a voltage upwards of 600mV and is limited on the top end by the minimum off-time and selected switching frequency.

The wide input voltage range makes it a suitable power supply option for a high current FPGA core and other general-purpose power solutions. The ISL73847SEH uses current mode modulation, which simplifies loop compensation and provides excellent power supply rejection. Additionally, the output is remotely sensed to compensate for any voltage drop in the load conditions. Together this results in a robust power supply solution that requires minimal components while achieving high current density.

The ISL73847SEH also features a tri-level output that provides excellent protection against faults by driving a mid-scale voltage to signal the power stage to enter a Hi-Z condition.

The ISL73847SEH operates across the military temperature range from -55°C to +125°C and is available in a 24 Ld hermetically sealed Ceramic Dual Flat-pack (CDFP) package or in die form.

Contents

1. SEE Testing

1.1 Objective

The testing was intended to find the limits of the pin voltages set by the onset of DSEE at a LET of 86MeV·cm^2/mg normal incidence Gold (^{197}Au). Additional testing was performed to identify and quantify SETs and SEFIs occurring on the output voltages. The irradiation for the SEE studies was completed with normal incidence Gold (^{197}Au) at a LET of 86MeV·cm^2/mg.

1.2 Facility

SEE testing was completed at the Texas A&M University (TAMU) Radiation Effects Facility of the Cyclotron Institute in College Station, Texas. This facility has a K500 superconducting cyclotron that can supply a wide range of ion species and flux. The testing referred to in this report was performed in April 2022 using the K500 cyclotron.

1.3 Setup

The ISL73847SEH was evaluated for SEE using a general-purpose engineering evaluation board that allowed the use of the 2-phase synchronous buck application configurations. The specific configurations changed with the type of testing. DSEE testing was performed using the 2-phase buck configuration operating at 500kHz. The SET testing was performed using the 2-phase buck configuration operating at 500kHz and 1000kHz.

The ISL73847SEH DUT (Device Under Test) irradiation setup is shown in Figure 1. The ISL73847SEH was configured for 2-phase operation at two PWM frequencies, each of which used a different board assembly. The board assembly configured for the switching frequency of 500kHz and V_{OUT} = 1.0V used an L_{OUTx} of 1.0µH and C_{OUT} of 880µF (4x KEMET T530D227M010ATE006-T with maximum ESR of 6mΩ each) The compensation component values were R_{COMP} = 4.22k, C_{COMP} = 10n, C_{POLE} = 330pF, R_{SLOPE} = 37.4k, and R_{DROOP} = 604Ω. The board assembly configured for the switching frequency of 1000kHz and V_{OUT} = 1.0V used a L_{OUTx} of 560nH. The rest of the components remained the same as for the 500kHz case.

The DSEE tests were performed on VDD, VCC, and ISENSE pins while monitoring the supply currents before and after irradiation. The VDD test started with VDD set to 23V, then VDD was incremented by 1V until the part exhibited permanent changes or until 25V was achieved. The VCC test started with VCC set to 6.1V, then VCC was incremented by 0.2V until the part exhibited permanent changes or until 6.7V was achieved. The ISENSE test started with V_{OUT} = ISENSE at 12V, then V_{OUT} = ISENSE was incremented by 0.5V until the part exhibited permanent changes or until 13V was achieved. The monitored parameters for the buck are listed in Table 1.

Table 1. Monitored Parameters and Failure Criteria for the ISL73847SEH DSEE Testing

Parameter Monitored	Deviation from Pre SEE testing for the following parameters	Post SEE Testing Failure Criteria
Buck Output Voltage	V_{OUT} = 1.0V	±2%
Enable pin current	I_VENPG = 2.2mA	±25%
VDD Supply current	I_VDD = 10mA	±25%

During the SET testing, the VDD supply operated at both 4.5V and 13.2V. The PVIN supply also operated at 4.5V and 13.2V during the SET testing. Scope 1 was set to trigger on events where V_{OUT} exceeded the ±2% window for SET events. Scope 2 was set to trigger on PGOOD events at a threshold of 2.25V on both edges. For detailed test conditions, see Table 5.

2. Results

2.1 Destructive Single Event Effects Data

The ISL73847SEH was tested for DSEE with normal incidence Gold (^{197}Au) at LET of 86MeV•cm^2/mg and a case temperature of 125°C ±10°C. The buck output of 1.0V was loaded to 5A..

Table 2 through Table 4 show a quick summary of the DSEE (including SEL) tests for the buck. Four devices were tested at 86MeV•cm^2/mg and passed with no DSEE to a fluence of 1E7 particles/cm^2 on each of the four parts. DSEE testing on a DUT was terminated when either a device failure or a change in the bias current for the pin under test was observed.

During the VDD DSEE testing, the DUT was irradiated starting with an initial VDD voltage of 23V with 1V increments until 25V was reached. No DSEE was seen at 25V. The results of the DSEE test are summarized in the Table 2.

Table 2. DSEE Test Results for VDD[1][2][3][4]

Run	DUT	V_{DD} (V)	V_{OUT} (V)		I_VENPG (mA)		I_VDD (mA)	
			Pre (V)	Post (V)	Pre (mA)	Post (mA)	Pre (mA)	Post (mA)
400	1	23	0.980	0.98	2.1	2.06	10.03	10.04
401	1	24	0.979	0.98	2.2	2.24	10.04	10.60
402	1	25	0.980	0.98	2.4	2.42	10.06	10.09
403	2	23	0.980	0.98	2.1	2.05	9.10	10.02
404	2	24	0.984	0.98	2.2	2.23	10.02	10.02
405	2	25	0.983	0.99	2.4	2.42	10.03	10.03
406	3	23	0.971	0.97	2.1	2.05	9.92	9.94
407	3	24	0.971	0.97	2.2	2.22	9.94	9.94
408	3	25	0.970	0.97	2.4	2.41	9.94	9.94
409	4	23	0.982	0.99	2.1	2.06	9.88	9.89
410	4	24	0.985	0.99	2.2	2.24	9.89	9.94
411	4	25	0.985	0.99	2.4	2.42	9.94	9.93

1. L_{OUT}/PHASE = 1µH, C_{OUT}/PHASE = 440µF, SYNCI = LOW, C_{VCC} = 0.68µF, C_{SS} = 22nF, R_{COMP} = 4.22k, C_{COMP} = 10nF, R_{PG} = 5k, R_{SLOPE} = 37.4k, EN = HIGH.
2. Switching Frequency set to 500kHz with R_{FS} = 92.4k.
3. DUT Biasing: PVIN = 5V, V_{BUS} = 6V, I_{OUT} = 5A.
4. Normal Incidence Gold (^{197}Au) at LET = 86MeV•cm^2/mg and 125°C ±10°C Case Temperature, with a run fluence of 1.00E+07particles/cm^2.

During the VCC DSEE testing, the DUT was irradiated starting with an initial VCC voltage of 6.1V with 0.2V increments until 6.7V was reached. No DSEE was seen at 6.7V. The results of the DSEE test are summarized in Table 3.

Table 3. DSEE Test Results for VCC [1][2][3][4]

Run	DUT	VCC (V)	VOUT (V)		I_VENPG (mA)		I_VCC (mA)	
			Pre (V)	Post (V)	Pre (nA)	Post (nA)	Pre (mA)	Post (mA)
412	5	6.1	0.988	0.99	950.0	950.00	11.66	11.68
413	5	6.3	0.989	0.99	950.0	940.00	12.30	12.26
414	5	6.5	0.991	0.99	940.0	960.00	13.02	13.01
415	5	6.7	0.991	0.99	960.0	970.00	13.92	13.89
416	6	6.1	0.973	0.97	1100.0	1100.00	11.79	11.78
417	6	6.3	0.975	0.98	1100.0	1100.00	12.42	12.41
418	6	6.5	0.976	0.98	1100.0	1100.00	13.11	13.16
419	6	6.7	0.973	0.97	1100.0	1100.00	14.05	14.04
420	7	6.5	0.974	0.97	1200.0	1200.00	13.07	13.07
421	7	6.7	0.970	0.97	1200.0	1200.00	13.96	13.94
422	8	6.5	0.987	0.99	600.0	600.00	13.05	13.02
423	8	6.7	0.986	0.99	600.0	600.00	13.91	13.88

1. L_{OUT}/PHASE = 1µH, C_{OUT}/PHASE = 440µF, SYNCI = LOW, C_{VCC} = 0.68µF, C_{SS} = 22nF, R_{COMP} = 4.22k, C_{COMP} = 10nF, R_{PG} = 5k, R_{SLOPE} = 37.4k, EN = HIGH.
2. Switching Frequency set to 500kHz with R_{FS} = 92.4k.
3. DUT Biasing: V_{DD} = V_{CC}, PVIN = 5V, V_{BUS} = 6V, I_{OUT} = 5A.
4. Normal Incidence Gold (^{197}Au) at LET = 86MeV•cm^2/mg and 125°C ±10°C Case Temperature, with a run fluence of 1.00E+07particles/cm^2.

During the ISENSE common-mode voltage DSEE testing, the DUT was irradiated starting with an initial V_{OUT} of 12V, which was incremented by 0.5V until 13.0V was reached. No DSEEs were observed when V_{OUT} was 12V on four devices. One device experienced a failure unrelated to ISENSE at 12.5V. The DSEE test setup had a scope set to monitor the V_{OUT} during the test. A few SEFI were observed at an ISENSE voltage of 12V. It should be noted that the SEFI characterization is only done during the SET testing. However, to determine the ISENSE threshold at which no SEFI are seen we tested a derivative device with the same ISENSE structure and found that the no SEFIs were observed at ISENSE = 10V and below. The results of the DSEE test are summarized in Table 4.

Table 4. DSEE Test Results for ISENSE[1][2][3][4]

Run	DUT	V_{OUT} (V)	V_{OUT} (V)		I_VDD mA)	
			Pre	Post	Pre	Post
424	9	12.0	12.068	12.080	48.000	48.000
425	9	12.5	12.570	0.000	48.500	48.000
426	10	12.0	11.985	12.010	47.700	48.000

Table 4. DSEE Test Results for ISENSE[1][2][3][4] (Cont.)

Run	DUT	V_{OUT} (V)	V_{OUT} (V)		I_VDD mA)	
			Pre	Post	Pre	Post
427	10	12.5	12.584	12.564	48.000	48.000
428	10	13.0	13.051	13.043	48.000	48.000
429	11	12.0	11.990	11.990	48.000	48.000
430	11	12.5	12.590	12.610	48.000	48.000
431	11	13.0	12.990	13.020	49.000	49.000
432	12	12.0	12.000	12.001	47.000	48.000
433	12	12.5	12.502	12.540	48.000	48.000
434	12	13.0	13.040	12.050	48.000	48.000

1. L_{OUT}/PHASE = 10µH, C_{OUT}/PHASE = 100µF, SYNCI = LOW, C_{VCC} = 0.68µF, C_{SS} = 22nF, R_{COMP} = 4.22k, C_{COMP} = 10nF, R_{PG} = 5k, R_{SLOPE} = 37.4k, EN = HIGH.
2. Switching Frequency set to 500kHz with R_{FS} = 92.4k.
3. DUT Biasing: V_{DD} = V_{CC} = 5V, PVIN = 25V, V_{BUS} = 6V, I_{OUT} = 5A.
4. Normal Incidence Gold (^{197}Au) at LET = 86MeV•cm^2/mg and 125°C ±10°C Case Temperature, with a run fluence of 1.00E+07particles/cm^2.

Both before and after irradiation three parameters (Table 1) were monitored to look for signs of DSEE. Table 2 through Table 4 show the results of DSEE testing for the device. Failures to the criteria at the top of the columns are indicated with a reduced sample count. For example with ISENSE = 12V, it had 4 of 4 devices passing; however, with ISENSE = 12.5V, 3 of 4 devices passed. The failed device did not show any change in the supply current; however, the V_{OUT} post radiation had no output voltage

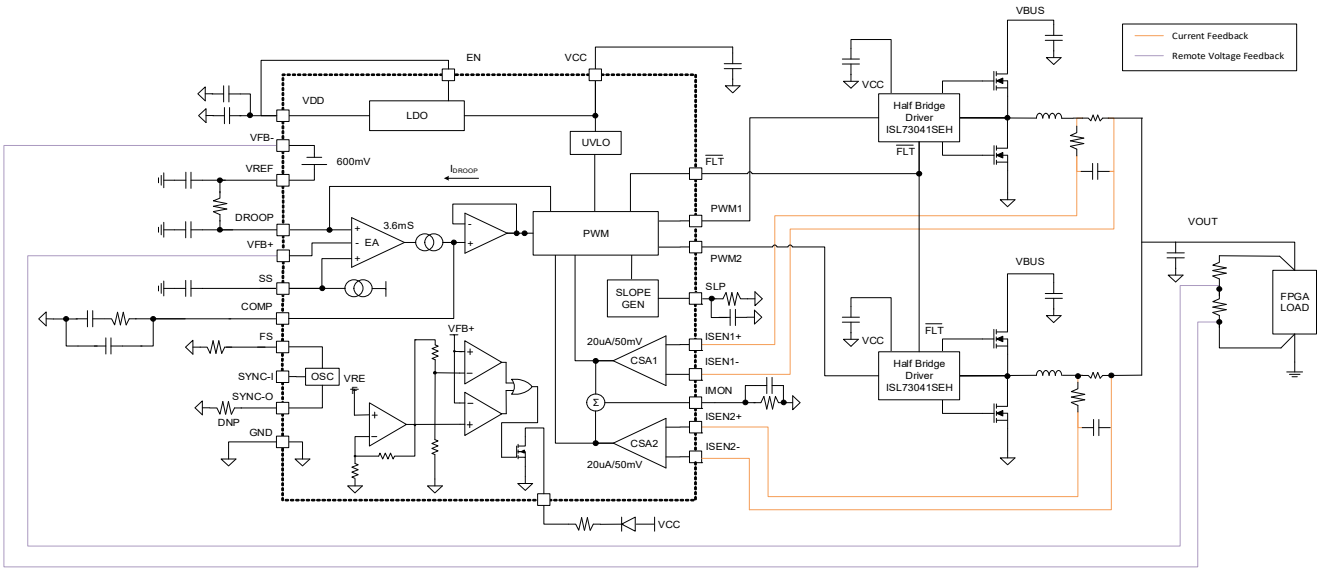

Figure 1. ISL73847SEH DUT SEE Irradiation Setup

2.2 Single Event Transient Data

The SET testing was performed on two devices at a f_{SW} of 500kHz and another two at an f_{SW} of 1000kHz. Each of the device runs were irradiated with normal incidence Gold (^{197}Au) for a LET of 86MeV•cm^2/mg to a fluence of 1E7particle/cm^2. The results of the tests performed for various conditions are in Table 5.

Table 5. SET Test Results [1][2][3][4]

Run	Switching Frequency (kHz)	DUT	V_{DD} (V)	PVIN (V)	V_{OUT} Pre RAD (V)	L_{OUT} (µH)	Scope1 CH1 = V_{OUT}, Trigger ±20mV	Scope2 CH1 = PG, Trigger ↑↓2.25V
							SET	SEFI
401	500	20	4.5	5.0	0.991	1.0	0	0
402	500	20	4.5	13.2	0.991	1.0	0	0
403	500	20	13.2	13.2	0.991	1.0	0	0
404	500	20	13.2	5.0	0.991	1.0	0	0
406	500	21	4.5	5.0	0.991	1.0	0	0
407	500	21	4.5	13.2	0.991	1.0	0	0
408	500	21	13.2	13.2	0.989	1.0	0	0
409	500	21	13.2	5.0	0.989	1.0	0	0
410	1000	30	4.5	5.0	0.992	0.56	0	0
411	1000	30	13.2	5.0	0.991	0.56	0	0
412	1000	31	4.5	5.0	0.989	0.56	0	0
413	1000	31	13.2	5.0	0.988	0.56	1	0

1. C_{OUT}/PHASE = 440µF, SYNCI = LOW, C_{VCC} = 0.68µF, C_{SS} = 22nF, R_{COMP} = 4.22k, C_{COMP} = 10nF, R_{PG} = 5k, R_{SLOPE} = 37.4k, EN = HIGH.
2. Switching Frequency set to 500kHz with R_{FS} = 92.4k and to 1000kHz with R_{FS} = 35.7k.
3. DUT Biasing: V_{BUS} = 6V, I_{OUT} = 5A.
4. Normal Incidence Gold (^{197}Au) at LET = 86MeV•cm^2/mg and 125°C ±10°C Case Temperature, with a run fluence of 1.00E+07particles/cm^2.

Figure 2 and Figure 3 show SET captures by backing down the ±20mV windows to ±8mV during the DSEE test at 125°C. No captures however were seen at 500kHz during the SET testing at 25°C with a ±20mV window trigger on V_{OUT}.

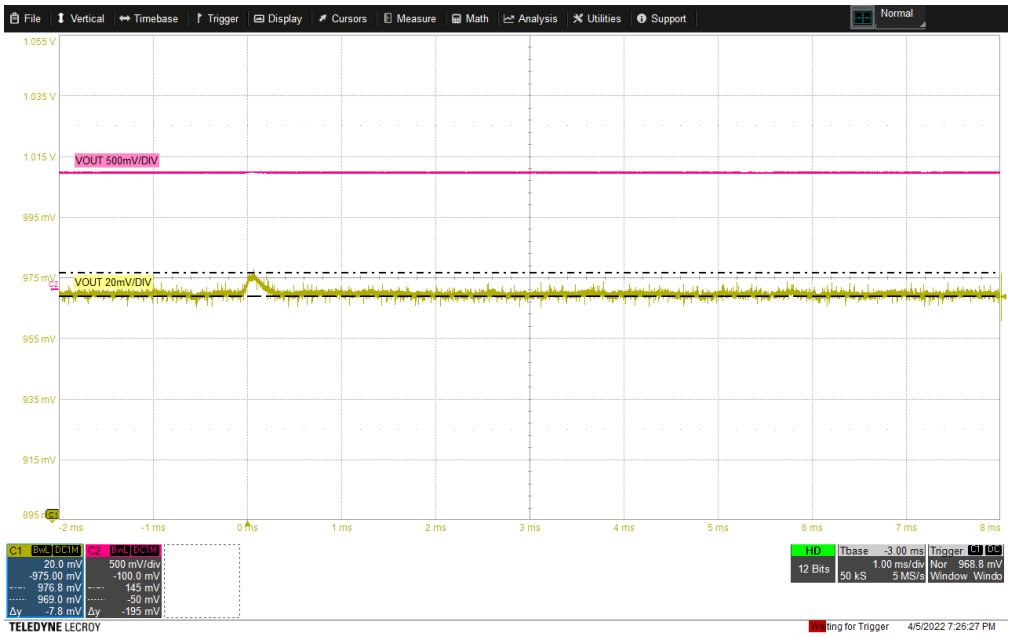

Figure 2. V_{OUT} SET = ±8mV during V_{DD} = 25V DSEE Test

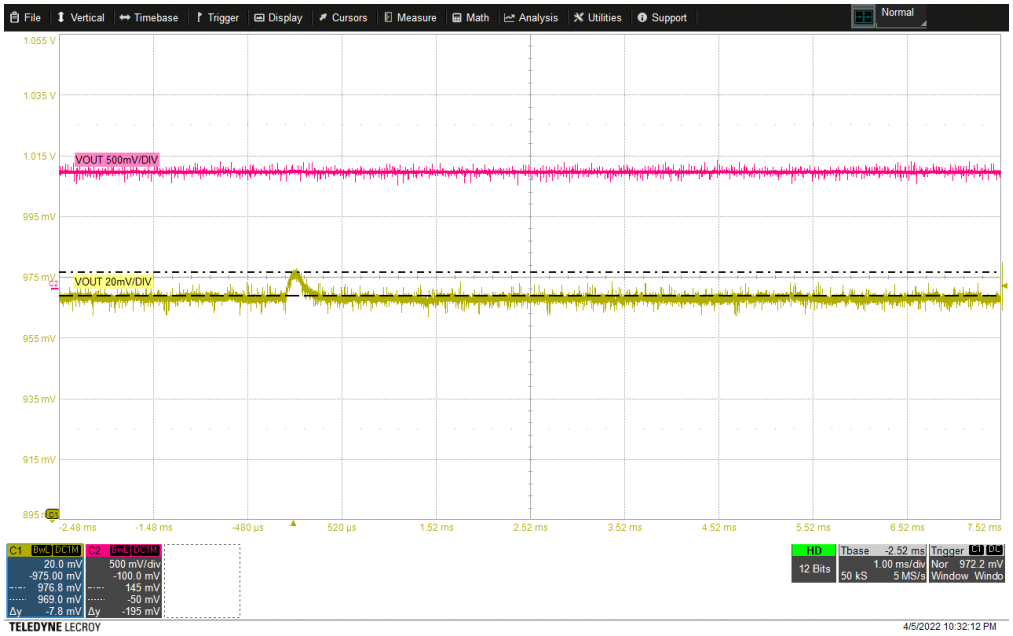

Figure 3. V_{OUT} SET = ±8mV during V_{CC} = 6.7V DSEE Test

Figure 4, shows the missing pulse on PWM2 captured during the test run 413. The signals monitored during the test were:

- PWM1 and PWM2 the drive signals.
- VREF the voltage reference (0.6V).
- SYNC-O is the output of the internal oscillator clock.
- COMP is the output of the error amplifier.
- DROOP the reference voltage to the error amplifier which is modulated in proportion to the current sensed by the controller.

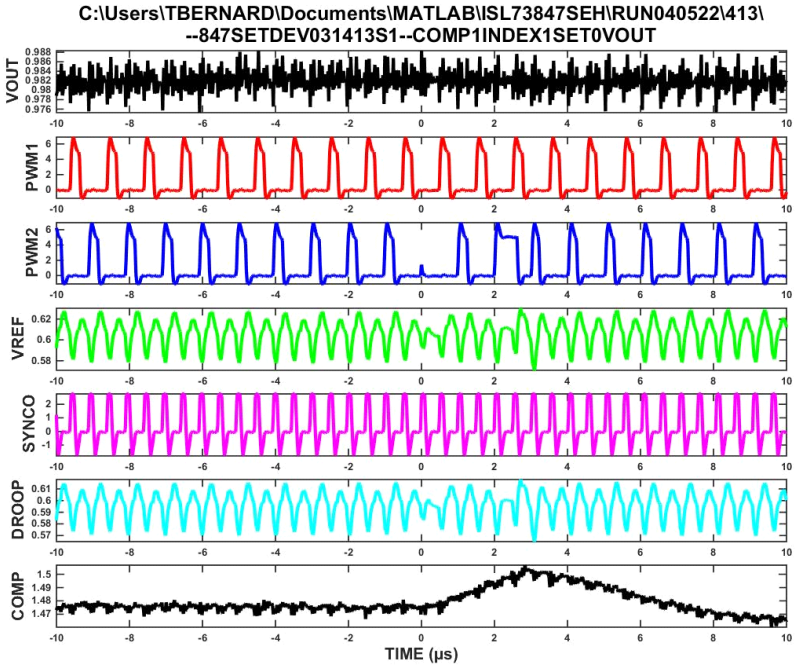

Figure 4. SET, LET86, f_{SW} = 1MHz, trigger V_{OUT} ±20mV

3. SEE Testing Summaries

3.1 Destructive Single Event Effects

DSEEs including SEL were tested with Gold (^{197}Au) at a LET of 86MeV•cm^2/mg to a Fluence of 1E7particles/cm^2 and a temperature of 125°C, for various values of VDD and VCC. The board assembly used a L_{OUTx} of 1.0µH and C_{OUT} of 880µF (4x KEMET T530D227M010ATE006-T with a maximum ESR of 6mΩ each). The compensation component values were set at R_{COMP} = 4.22k, C_{COMP} = 10n, C_{POLE} = 330pF, R_{SLOPE} = 37.4k, and R_{DROOP} = 604Ω.

The VOUT of 1V was loaded to 5A. The VDD and VCC voltages were varied for the respective DSEE tests. Results of the individual tests are that:

- No DSEE including SEL were observed V_{DD} = 25V to a fluence of 1E7 particles/cm^2 on each of the four units.
- No DSEE including SEL were observed V_{CC} = 6.7V to a fluence of 1E7 particles/cm^2 on each of the four units.

DSEEs including SEL were tested with Gold (^{197}Au) to a LET of 86MeV·cm^2/mg at a temperature of 125°C and various values of ISENSE. The board assembly used a L_{OUTx} of 10µH and C_{OUT} of 200µF (2x KEMET T521X107M025ATE030 with a maximum ESR of 30mΩ each). The compensation component values were set at R_{COMP} = 4.22k, C_{COMP} = 47n, C_{POLE} = 330pF, R_{SLOPE} = 76.8k, R_{DROOP} = 0Ω. An incremental voltage was

applied to the VB+ node to vary the V_{OUT} starting at 12V and thereby the common-mode voltage on the ISENSE pin.

- No SEFI seen at ISENSE = 10V. SEFI was observed at the ISENSE voltage of 12V. To determine the threshold for ISENSE at which no SEFI were seen, we tested a derivative device with the same ISENSE structure. It was found that the no SEFI was observed at ISENSE = 10V.

3.2 Single Event Transients

The SEE Testing for the ISL73847SEH was performed at TAMU. The DUT was configured for a switching frequency of 500kHz and was tested for SETs with Gold (^{197}Au) at a LET of 86MeV·cm^2/mg to a fluence of 1E7particles/cm^2. The board assembly used a LOUTx of 1.0µH and COUT of 880µF (4x KEMET T530D227M010ATE006-T with a maximum ESR of 6mΩ each) The compensation component values were set at R_{COMP} = 4.22k, C_{COMP} = 10n, C_{POLE} = 330pF, R_{SLOPE} = 37.4k, and R_{DROOP} = 604Ω. The DUT VDD was biased at 4.5V and 13.2V, and the PVIN was biased at 5V and 13.2V. The V_{OUT} of 1V was loaded to 5A. The SET trigger capture window was set to ±20mV (±2%) for V_{OUT} = 1.0V. The observation was that no SET was captured at a Fluence of 1E7 particles/cm^2 on each of the four parts.

The DUT configured for a switching frequency of 1000kHz was tested for SETs with Gold (^{197}Au) at an LET of 86MeV•cm^2/mg to a fluence of 1E7particles/cm^2. The board assembly used a L_{OUTx} of 0.56µH and C_{OUT} of 880µF (4x KEMET T530D227M010ATE006-T with a maximum ESR of 6mΩ each) The compensation component values were set the same as the 500kHz case. The DUT VDD was biased at 4.5V and 13.2V, and the PVIN was biased at 5V and 13.2V. The VOUT of 1V was loaded to 5A. The SET trigger capture window was set to ±20mV (±2%) for V_{OUT} = 1.0V. The observation was that a single SET event was captured at a Fluence of 1E7 particles/cm^2 on run 413. See Table 5 and Figure 4 for more details. The missing pulse was observed on PWM2, while PWM1 was normal. The trigger event was noise spike at the trigger point, the V_{OUT} did not show movement in the ±20mV window. It should be noted that the conditions for run 411 were the same as that of 413 and we did not observe an SET event.

Based on CRÈME simulations for a GEO orbit, statistically speaking, the part would expect to experience a particle with LET ≥ 86MeV•cm^2/mg once about every 58000 years. In a typical LEO, it would be about once every 2 million years.

4. Revision History

Revision	Date	Description
1.00	Nov 4, 2022	Initial release.

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